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1. General description

NPN/PNP Resistor-Equipped double Transistors (RET) in an ultra small DFN1412-6 (SOT1268) leadless Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PRMH12.

2. Features and benefits

- · 100 mA output current capability
- · Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- · Reduces pick and place costs
- Low package height of 0.5 mm
- AEC-Q101 qualified

3. Applications

- Digital applications
- Cost-savings alternative to BC847/BC857 series digital applications
- · Control of IC inputs
- Switching loads

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transisto	Per transistor, for the PNP transistor with negative polarity								
V _{CEO}	collector-emitter voltage	open base		-	-	50	V		
Io	output current			-	-	100	mA		
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 5 mA; T_{amb} = 25 °C		80	-	-			
R1	bias resistor 1	T _{amb} = 25 °C	[1]	33	47	61	kΩ		
R2/R1	bias resistor ratio		[1]	0.8	1	1.2			

[1] See section "Test information" for resistor calculation and test conditions.



50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1	7 6	
3	O2	output (collector) TR2	2 5	R1 R2
4	GND2	GND (emitter) TR2		TR1 TR2
5	12	input (base) TR2	3 6 4	R2 R1
6	01	output (collector) TR1	Transparent top view	
7	O1	output (collector) TR1	DFN1412-6 (SOT1268)	GND1 I1 O2
8	O2	output (collector) TR2	, ,	aaa-007379

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PRMD12	DFN1412-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body: 1.4 mm x 1.2 mm x 0.47 mm	SOT1268		

7. Marking

Table 4. Marking codes

Type number	Marking code
PRMD12	B2

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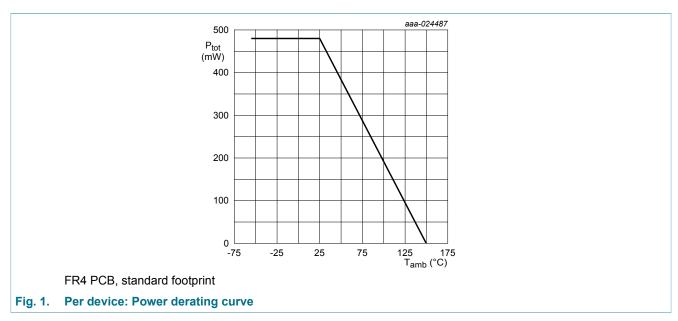
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or, for the PNP transistor wit	h negative polarity	,			_
V _{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	10	V
VI	input voltage	positive		-	40	V
		negative		-	-10	V
Io	output current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
Per device				'		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	480	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	tor					,	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	385	K/W
Per device	,						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	261	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

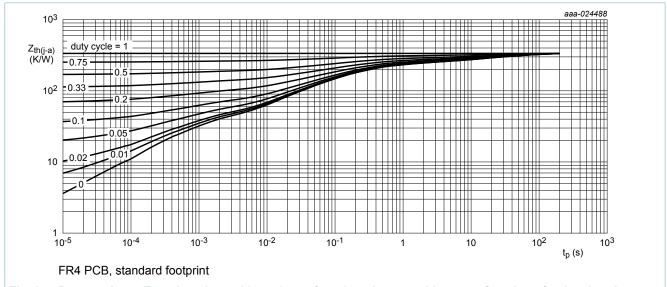


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

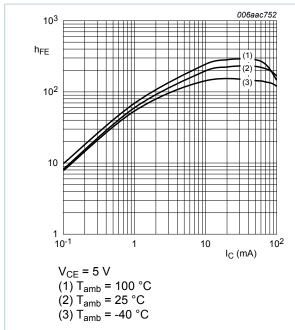
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or, for the PNP transistor v	with negative polarity			-	,	
I _{CBO}	collector-base cut-off current (emitter open)	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	nA
I _{CEO}	collector-emitter cut-off	V_{CE} = 30 V; I_{B} = 0 A; T_{amb} = 25 °C		-	-	1	μΑ
	current (base open)	V_{CE} = 30 V; I_{B} = 0 A; T_{j} = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current (collector open)	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	90	μΑ
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 5 mA; T_{amb} = 25 °C		80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	150	mV
$V_{I(off)}$	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C		-	1.2	8.0	V
V _{I(on)}	on-state input voltage	V_{CE} = 0.3 V; I_{C} = 2 mA; T_{amb} = 25 °C		3	1.6	-	V
R1	bias resistor 1	T _{amb} = 25 °C	[1]	33	47	61	kΩ
R2/R1	bias resistor ratio		[1]	0.8	1	1.2	
C _C	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	2.5	pF
		V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	3	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	230	-	MHz
		V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	180	-	MHz

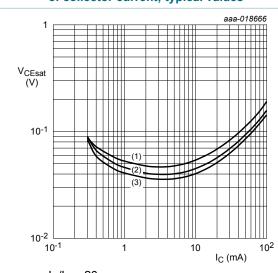
^[1] See section "Test information" for resistor calculation and test conditions.

^[2] Characteristics of built-in transistor.

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)



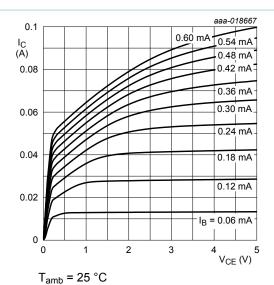
NPN transistor: DC current gain as a function Fig. 3. of collector current; typical values



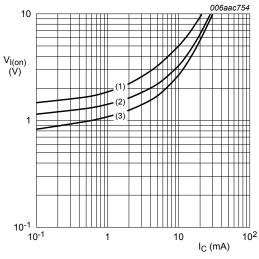
 $I_C/I_B = 20$ (1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \,^{\circ}\text{C}$ (3) $T_{amb} = -40 \,^{\circ}\text{C}$

Fig. 5. **NPN Transistor: Collector-emitter saturation** voltage as a function of collector current; typical values



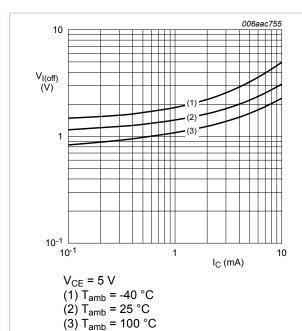
NPN Transistor: Collector current as a function Fig. 4. of collector-emitter voltage; typical values



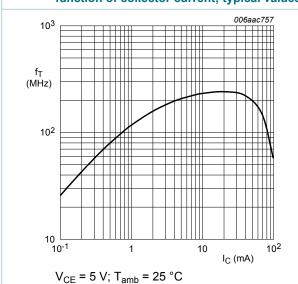
 $V_{CE} = 0.3 \text{ V}$ (1) $T_{amb} = -40 \,^{\circ}\text{C}$ (2) $T_{amb} = 25 \,^{\circ}\text{C}$ (3) $T_{amb} = 100 \,^{\circ}\text{C}$

NPN transistor: On-state input voltage as a Fig. 6. function of collector current; typical values

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NPN transistor: Off-state input voltage as a Fig. 7. function of collector current; typical values



NPN transistor: Transition frequency as a Fig. 9. function of collector current; typical values of built-in transistor

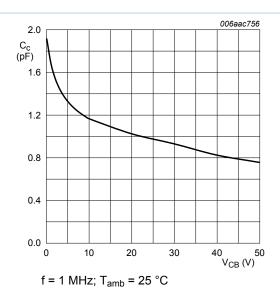
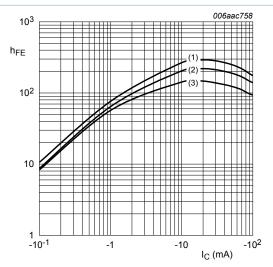


Fig. 8. NPN transistor: Collector capacitance as a function of collector-base voltage; typical values



V_{CE} = -5 V (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 10. PNP transistor: DC current gain as a function of collector current; typical values

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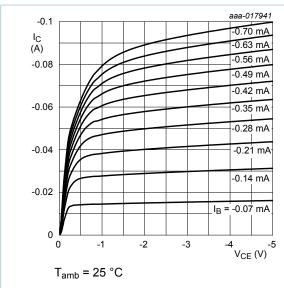
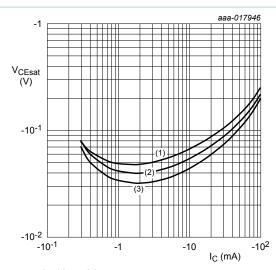
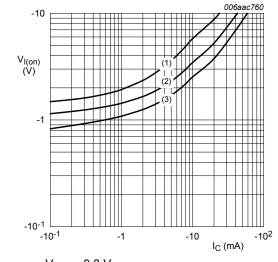


Fig. 11. PNP transistor: Collector current as a function of collector-emitter voltage; typical values



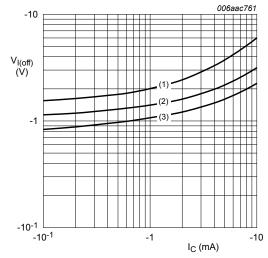
 $I_{C} / I_{B} = 20$ (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 12. PNP transistor: Collector-emitter saturation voltage as a function of collector current; typical values



 V_{CE} = -0.3 V(1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 13. PNP transistor: On-state input voltage as a function of collector current; typical values



 V_{CE} = -5 V

(1) T_{amb} = -40 °C (2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 14. PNP transistor: Off-state input voltage as a function of collector current; typical values

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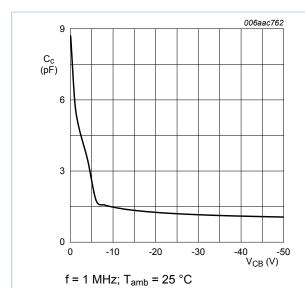


Fig. 15. PNP transistor: Collector capacitance as a function of collector-base voltage; typical values

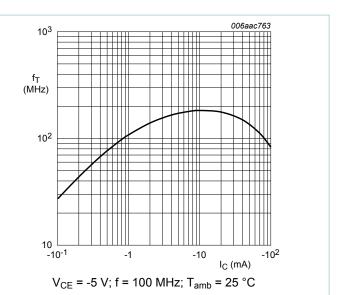


Fig. 16. PNP transistor: Transition frequency as a function of collector current; typical values of built-in transistor

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

· Calculation of bias resistor 1 (R1)

$$RI = \frac{V(I_{12}) - V(I_{11})}{I_{12} - I_{11}}$$

Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

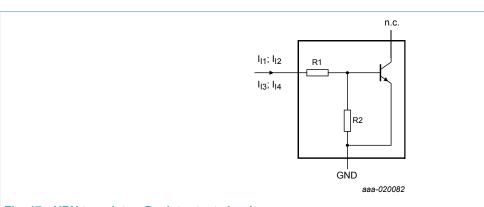
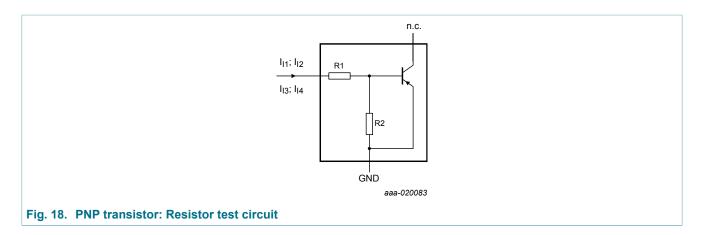


Fig. 17. NPN transistor: Resistor test circuit

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Resistor test conditions

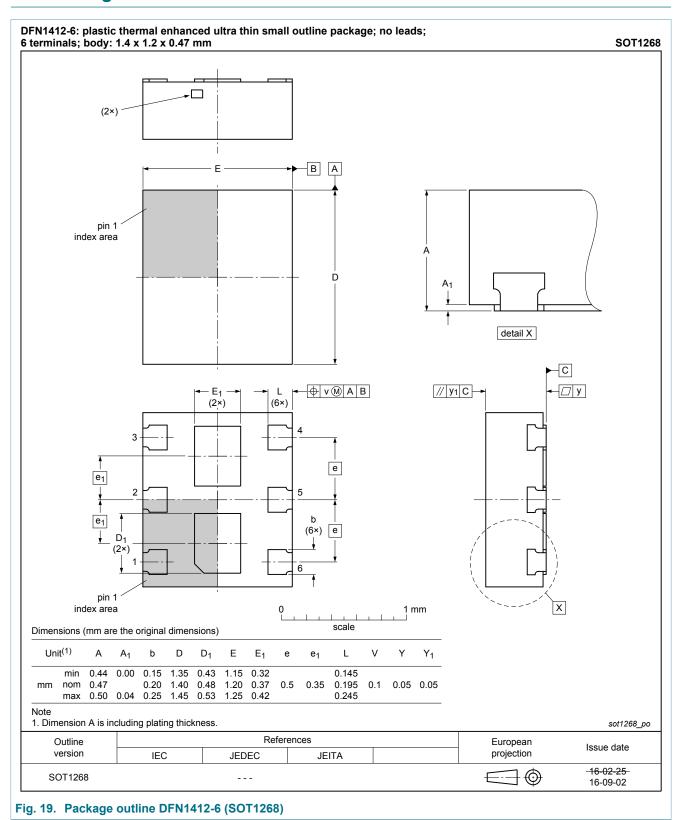
Table 8. Resistor test conditions

Per transistor; for the PNP transistor with negative polarity

R1 (kΩ)	R2 (kΩ)	Test conditions	est conditions					
		I _{I1}	I ₁₂	I ₁₃	I ₁₄			
47	47	55 µA	105 μΑ	-55 μΑ	-150 μΑ			

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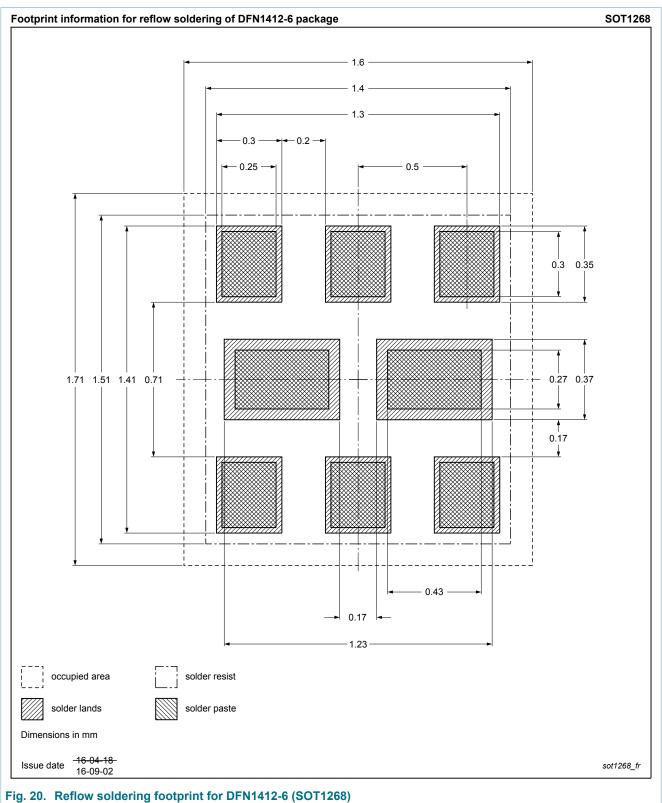
12. Package outline



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13. Soldering



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14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PRMD12 v.1	20170711	Product data sheet	-	-

50 V, 100 mA NPN/PNP Resistor-Equipped double Transistors (RET)

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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